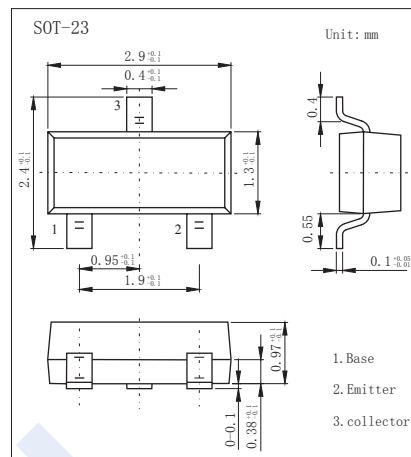


PNP Transistors

2SA1182

■ Features

- Collector Current Capability $I_C = -0.5A$
- Collector Emitter Voltage $V_{CE0} = -32V$
- Complementary to 2SC2859.

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-40	V
Collector - Emitter Voltage	V_{CE0}	-32	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_C	-500	mA
Base Current - Continuous	I_B	-50	
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_J	125	$^\circ C$
Storage Temperature range	T_{stg}	-55 to 125	

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100 \mu A, I_E = 0$	-40			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -1 mA, I_B = 0$	-32			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100 \mu A, I_C = 0$	-5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -40 V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100 mA, I_B = -10mA$		-0.1	-0.25	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100 mA, I_B = -10mA$			-1.2	
Base-emitter voltage	V_{BE}	$V_{CE} = -1V, I_C = -100 mA$		-0.8	-1	
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -100mA$	70		400	
	$h_{FE(2)}$	$V_{CE} = -6V, I_C = -400mA$ *1	25		25	
Collector output capacitance	C_{ob}	$V_{CB} = -6V, I_E = 0, f = 1MHz$		13		pF
Transition frequency	f_T	$V_{CE} = -6V, I_C = -20mA$		200		MHz

*1: $h_{FE(2)}$ classification O: 25 (min), Y: 40 (min), GR: 70 (min)

■ Classification of $h_{FE(1)}$

Marking	ZO	ZY	ZG
Rank	O	Y	GR(G)
Range	70-140	120-240	200-400

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■ Typical Characteristics

